

ABSTRACT

SEMICONDUCTOR MEMORY DEVICE AND METHOD FOR FORMING THE SAME

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A semiconductor memory device includes a stacked structure including a plurality of conductive layers and a plurality of interlayer insulating layers, which are alternately stacked on a substrate; stepped grooves provided in the stacked structure, the stepped grooves having
10 different depths from each other; and an opening portion penetrating the stacked structure to contact the substrate and having steps on sidewalls, the steps having heights corresponding to depth differences between stepped grooves.

15 FIG. 6